

Dual N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

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	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
Channel-1	30	0.019 at V _{GS} = 10 V	8.0
		0.026 at V _{GS} = 4.5 V	6.9
Channel-2		0.035 at V _{GS} = 10 V	6.0
		0.048 at V _{GS} = 4.5 V	5.0

FEATURES

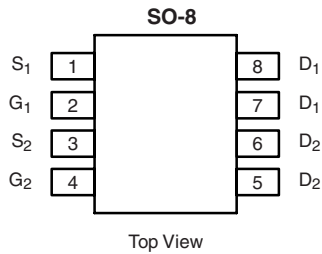
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs
- 100 % R_g Tested

APPLICATIONS

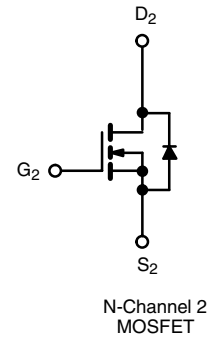
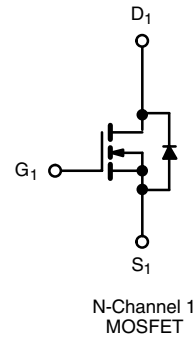
- Logic DC/DC
- Notebook PC



RoHS
COMPLIANT
HALOGEN
FREE
Available



Ordering Information: Si4974DY-T1-E3 (Lead (Pb)-free)
Si4974DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

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Parameter		Symbol	Channel-1		Channel-2		Unit
			10 s	Steady State	10 s	Steady State	
Drain-Source Voltage		V _{DS}	30				V
Gate-Source Voltage		V _{GS}	± 20				
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 25 °C	I _D	8.0	6.0	6.0	4.4	A
	T _A = 70 °C		6.5	4.7	4.8	3.5	
Pulsed Drain Current		I _{DM}	40		30		
Continuous Source Current (Diode Conduction) ^a		I _S	1.8	1.0	1.8	1.0	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	15		7		
Avalanche Energy		E _{AS}	11		2.45		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	2	1.1	2	1.1	W
	T _A = 70 °C		1.3	0.7	1.3	0.7	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150				°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Channel-1		Channel-2		Unit
		Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient ^a	R _{thJA}	50	62.5	52	62.5	°C/W
		90	110	91	110	
Maximum Junction-to-Foot (Drain)	R _{thJF}	30	40	32	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

MOSFET SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit
Static							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	Ch-1	1.0		3.0	V
			Ch-2	1.0		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	Ch-1			± 100	nA
			Ch-2			± 100	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	Ch-1			1	μA
			Ch-2			1	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			15	
			Ch-2			15	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	Ch-1	20			A
			Ch-2	20			
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 8.0 A	Ch-1		0.016	0.019	Ω
		V _{GS} = 10 V, I _D = 6.0 A	Ch-2		0.029	0.035	
		V _{GS} = 4.5 V, I _D = 6.9 A	Ch-1		0.0215	0.026	
		V _{GS} = 4.5 V, I _D = 5.0 A	Ch-2		0.040	0.048	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 8.0 A	Ch-1		19		S
		V _{DS} = 15 V, I _D = 6.0 A	Ch-2		13		
Diode Forward Voltage ^b	V _{SD}	I _S = 1.8 A, V _{GS} = 0 V	Ch-1		0.8	1.1	V
		I _S = 1.8 A, V _{GS} = 0 V	Ch-2		0.8	1.1	
Dynamic ^a							
Total Gate Charge	Q _g	Channel-1 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 8.0 A	Ch-1		7.0	11	nC
			Ch-2		3.3	5	
Gate-Source Charge	Q _{gs}	Channel-2 V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 6.0 A	Ch-1		2.6		
			Ch-2		1.2		
Gate-Drain Charge	Q _{gd}		Ch-1		3.0		
			Ch-2		1.5		
Gate Resistance	R _g		Ch-1	0.8	1.5	2.3	Ω
			Ch-2	0.9	1.95	2.9	
Turn-On Delay Time	t _{d(on)}	Channel-1 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω	Ch-1		8	15	ns
			Ch-2		6	10	
Rise Time	t _r		Ch-1		12	20	
			Ch-2		11	18	
Turn-Off Delay Time	t _{d(off)}	Channel-2 V _{DD} = 15 V, R _L = 15 Ω I _D ≅ 1 A, V _{GEN} = 10 V, R _G = 6 Ω	Ch-1		22	35	
			Ch-2		15	25	
Fall Time	t _f		Ch-1		6	10	
			Ch-2		6	10	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.8 A, dI/dt = 100 A/μs	Ch-1		20	40	
			Ch-2		15	30	

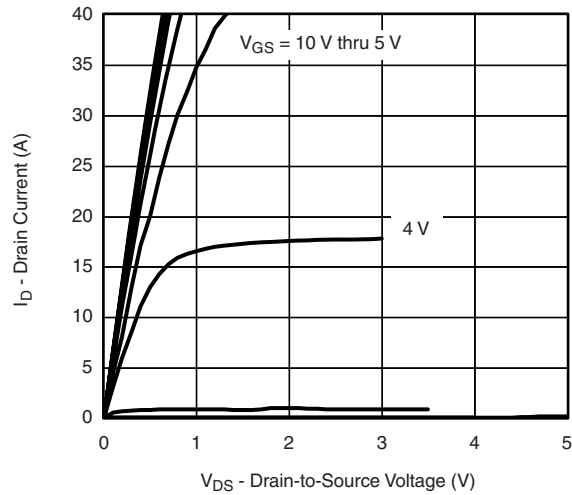
Notes:

a. Guaranteed by design, not subject to production testing.

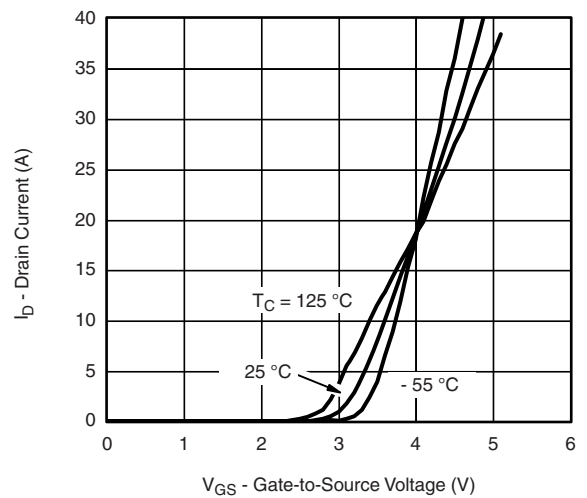
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

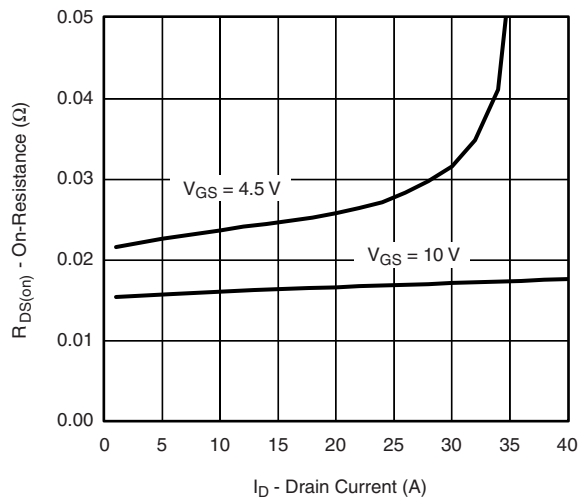
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



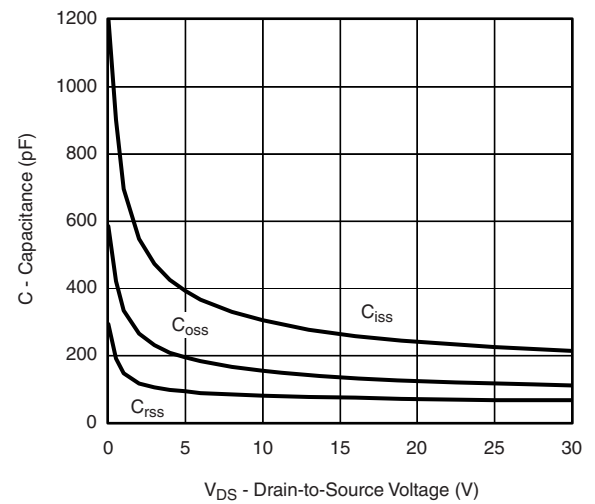
Output Characteristics



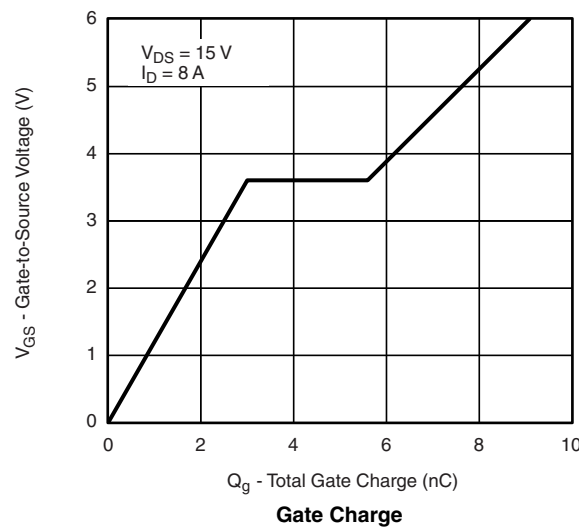
Transfer Characteristics



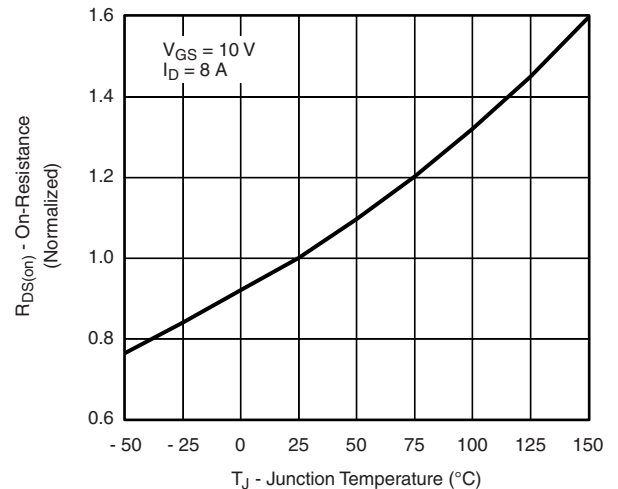
On-Resistance vs. Drain Current



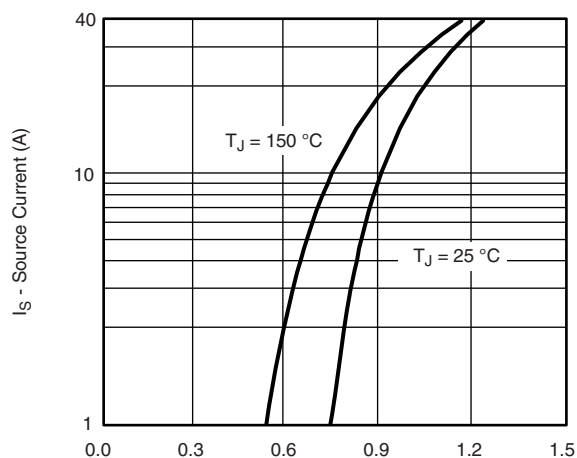
Capacitance



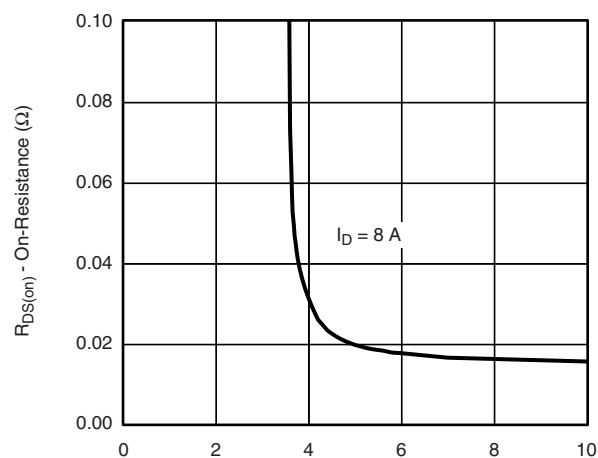
Gate Charge



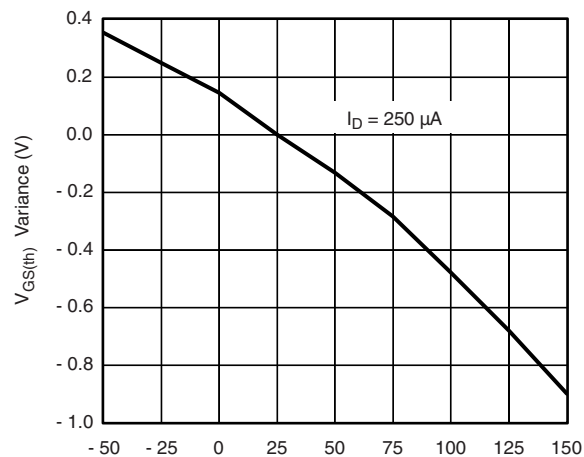
On-Resistance vs. Junction Temperature

CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

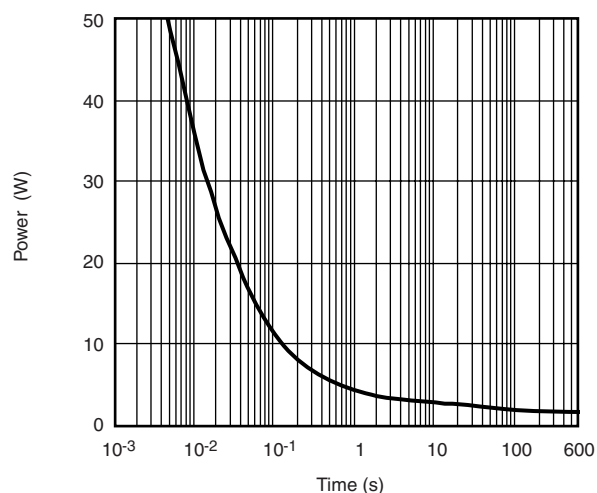
Source-Drain Diode Forward Voltage



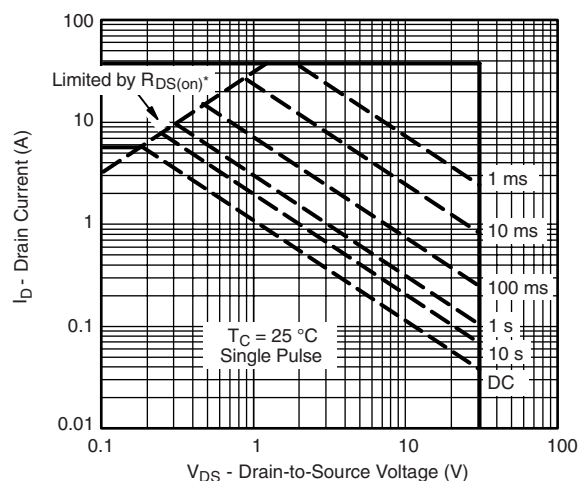
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



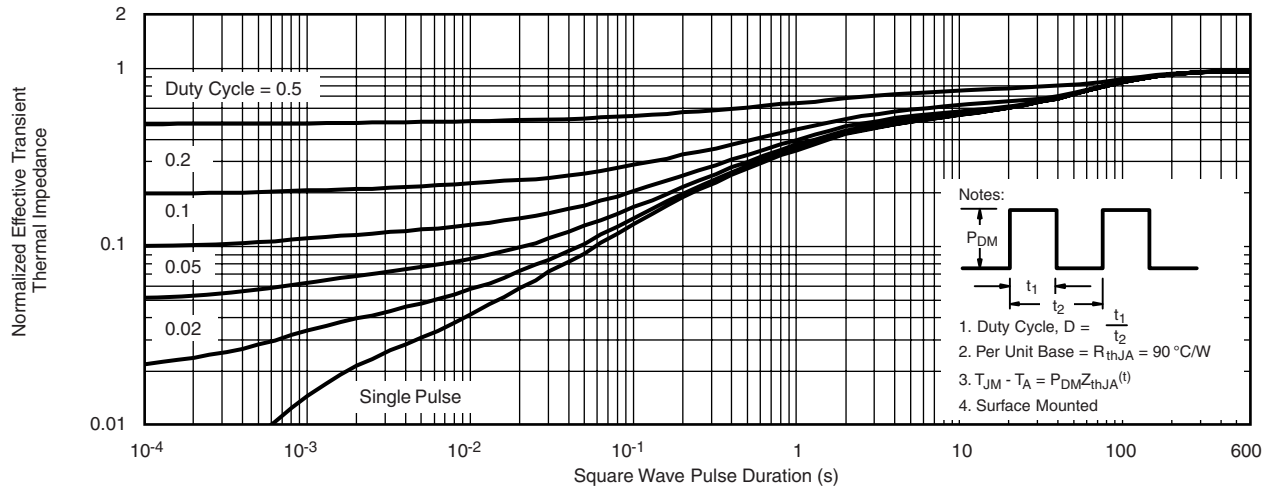
Single Pulse Power



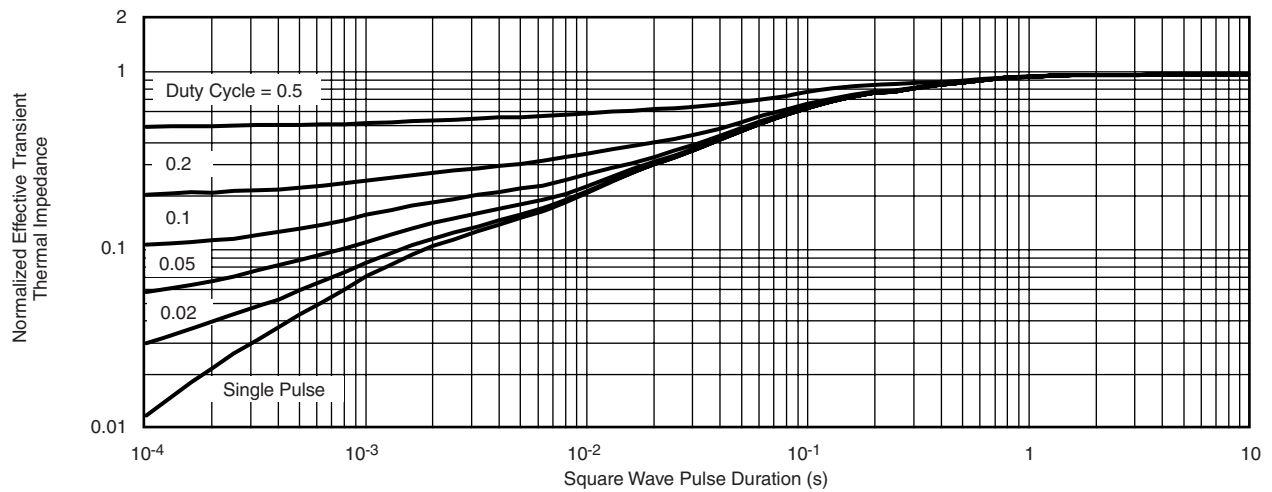
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

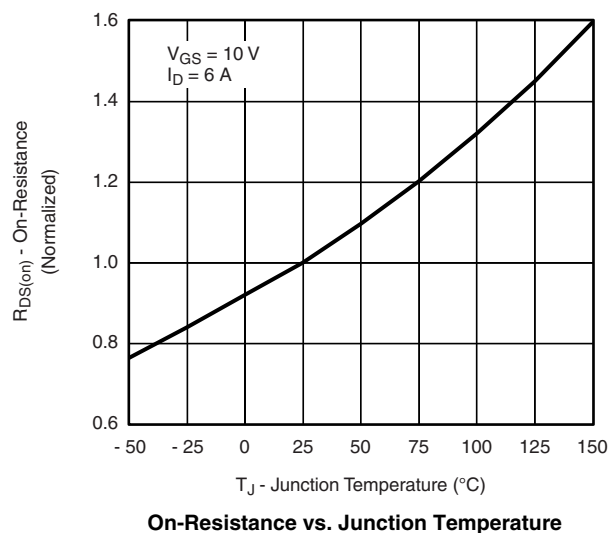
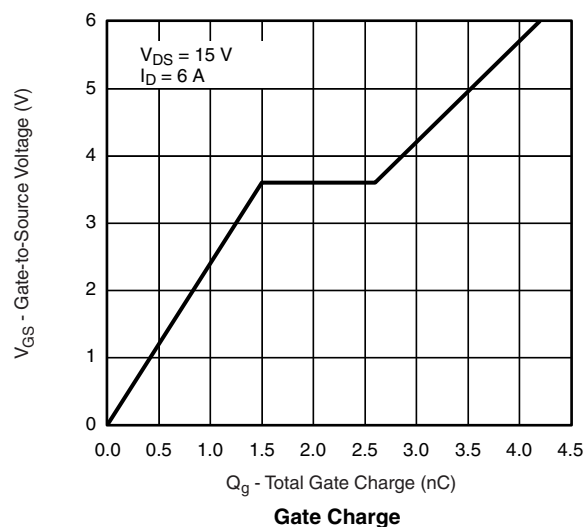
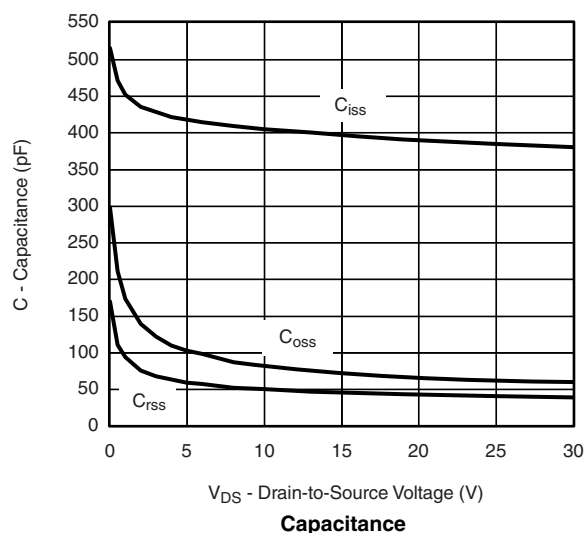
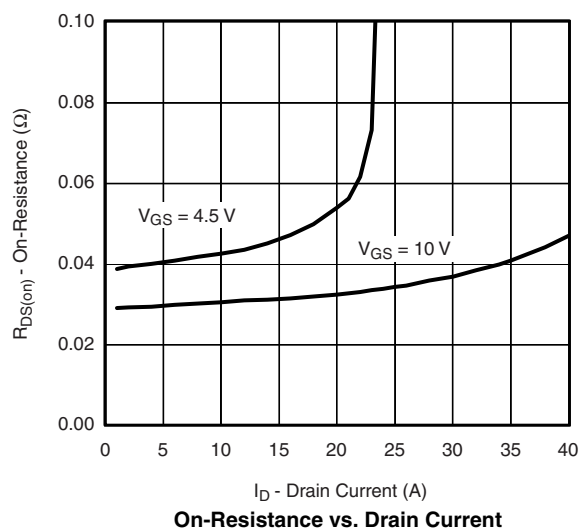
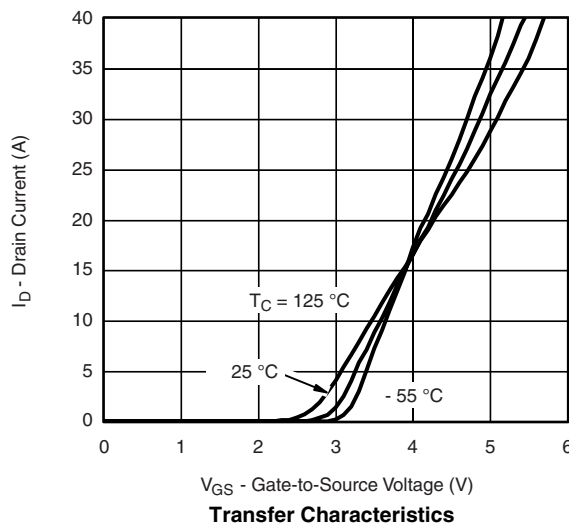
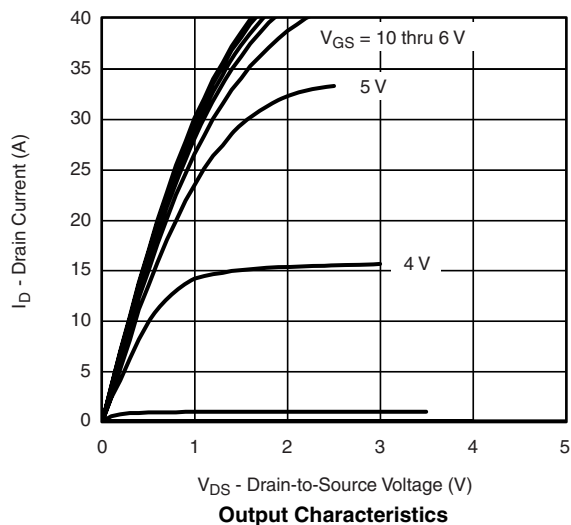
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



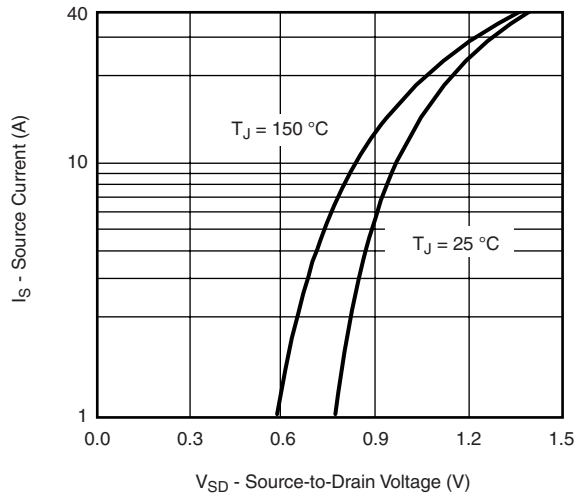
Normalized Thermal Transient Impedance, Junction-to-Ambient



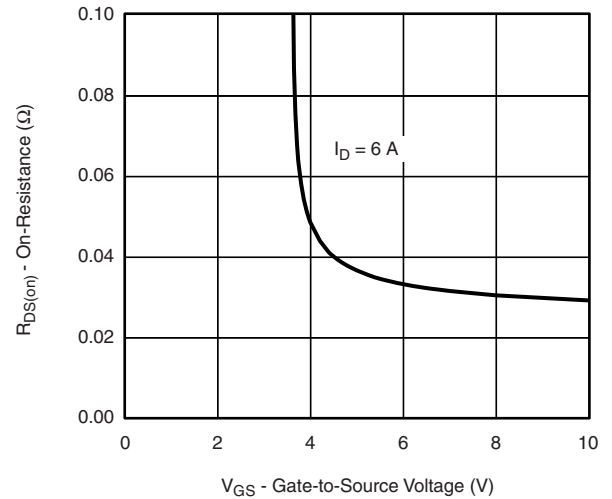
Normalized Thermal Transient Impedance, Junction-to-Foot

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

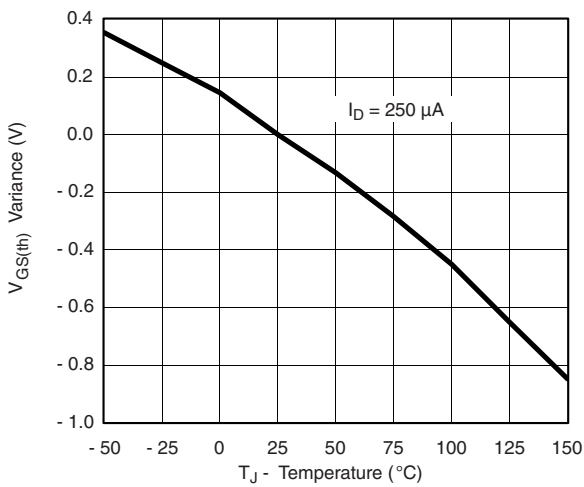
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



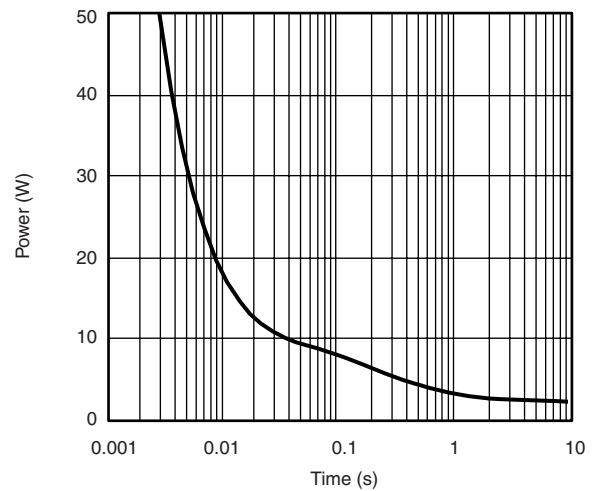
Source-Drain Diode Forward Voltage



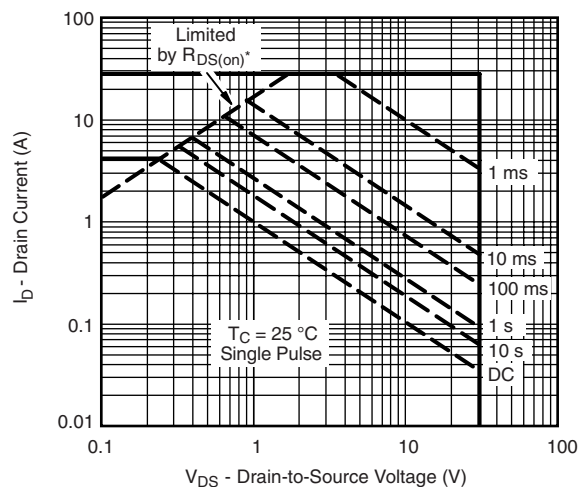
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

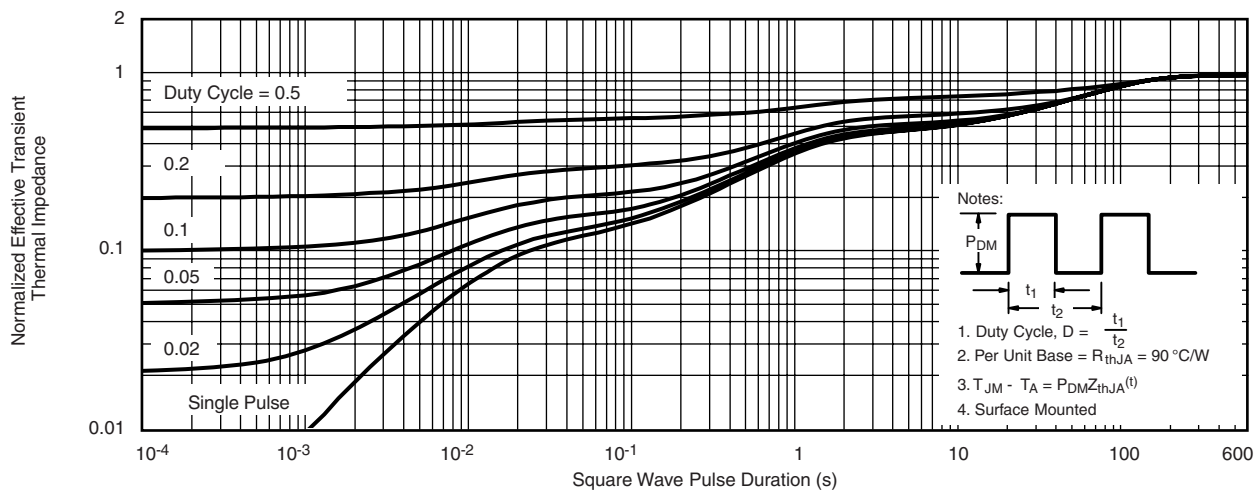
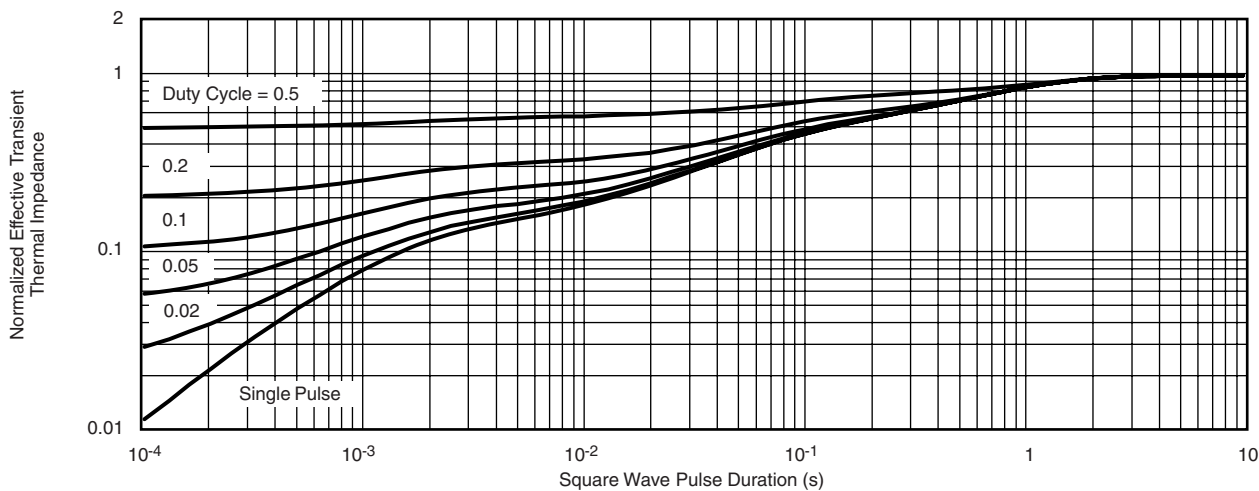


Single Pulse Power, Junction-to-Ambient



* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Foot**

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